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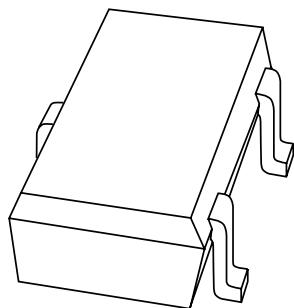
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Kind regards,

Team Nexperia

DATA SHEET



PMST2369 NPN switching transistor

Product data sheet
Supersedes data of 1997 May 05

1999 Apr 22

NXP
founded by Philips

NPN switching transistor

PMST2369

FEATURES

- Low current (max. 200 mA)
- Low voltage (max. 15 V).

APPLICATIONS

- High-speed switching applications, primarily in portable and consumer equipment.

DESCRIPTION

NPN switching transistor in a SOT323 plastic package.

MARKING

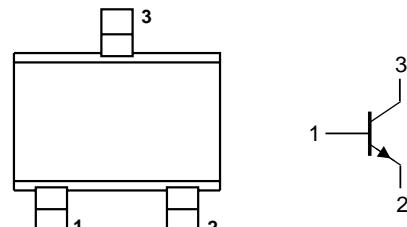
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMST2369	*1J

Note

1. * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



Top view MAM062

Fig.1 Simplified outline (SOT323) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	200	mA
I_{CM}	peak collector current	$t_p \leq 10 \mu\text{s}$	–	300	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{\text{amb}} \leq 25^\circ\text{C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 $T_{amb} = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 20\text{ V}$	—	400	nA
		$I_E = 0$; $V_{CB} = 20\text{ V}$; $T_j = 125^\circ\text{C}$	—	30	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 4\text{ V}$	—	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ mA}$; $V_{CE} = 1\text{ V}$	40	120	
		$I_C = 10\text{ mA}$; $V_{CE} = 1\text{ V}$; $T_{amb} = -55^\circ\text{C}$	20	—	
		$I_C = 100\text{ mA}$; $V_{CE} = 2\text{ V}$; note 1	20	—	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}$; $I_B = 1\text{ mA}$	—	250	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}$; $I_B = 1\text{ mA}$	700	850	mV
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 5\text{ V}$; $f = 1\text{ MHz}$	—	4	pF
f_T	transition frequency	$I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$	500	—	MHz

Switching times (between 10% and 90% levels); (see Fig.2)

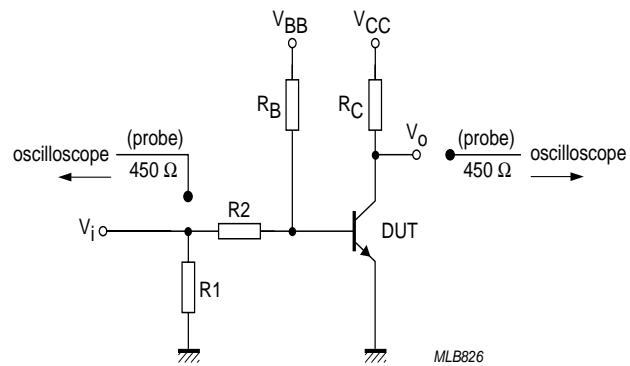
t_{on}	turn-on time	$I_{Con} = 10\text{ mA}$; $I_{Bon} = 3\text{ mA}$; $I_{Boff} = -1.5\text{ mA}$	—	10	ns
t_d	delay time		—	4	ns
t_r	rise time		—	6	ns
t_{off}	turn-off time		—	20	ns
t_s	storage time		—	10	ns
t_f	fall time		—	10	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

NPN switching transistor

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V_i = 0.5 V to 4.2 V; T = 500 μ s; t_p = 10 μ s; t_r = t_f \leq 1 ns.

R_1 = 56 Ω ; R_2 = 1 k Ω ; R_B = 1 k Ω ; R_C = 270 Ω .

V_{BB} = 0.2 V; V_{CC} = 2.7 V.

Oscilloscope: input impedance Z_i = 50 Ω .

Fig.2 Test circuit for switching times.

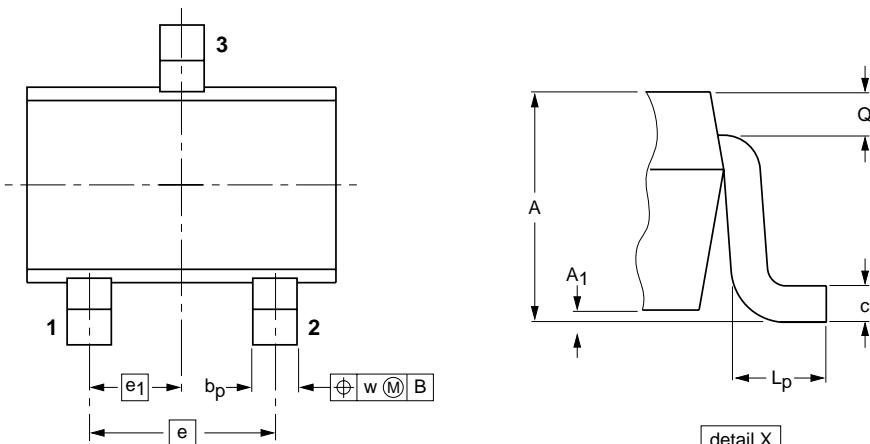
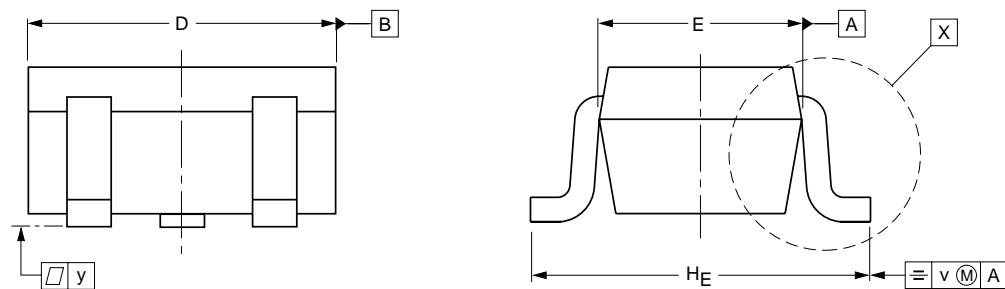
NPN switching transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



0 1 2 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ	SC-70		
SOT323						97-02-28

NPN switching transistor

PMST2369

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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Contact information

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